NSN 5961-00-488-4832

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View Online at https://aerobasegroup.com/nsn/5961-00-488-4832	
Inclosure Material:	
Ceramic and metal and glass	
Overall Length:	
Between 0.102 inches and 0.115 inches	
Overall Diameter:	
Between 0.084 inches and 0.092 inches	
Mounting Method:	
Press fit	
Features Provided:	
Hermetically sealed case and gold plated leads	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
50.0 collector to emitter voltage/static/base open and 7.0 emitter to collector voltage, do	;
Current Rating Per Characteristic:	
1.00 microamperes emitter current, dc peak	
Power Rating Per Characteristic:	
50.0 milliwatts small-signal input power, common-collector preset	
Maximum Operating Tempurature Per Measurement Point:	
125.0 degrees celsius ambient air	
Precious Material And Location:	
Case and tab surfaces gold	
Precious Material:	
Gold	
Terminal Type And Quantity:	
2 tab, solder lug and 1 case	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
Yes - demil/mli	
Fiig:	